

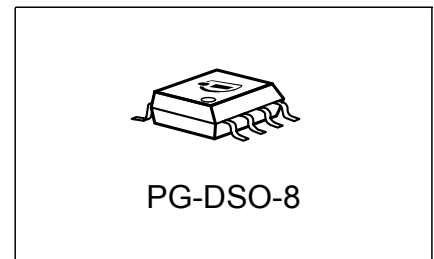
Smart Power High-Side-Switch for Industrial Applications

Features

- Overload protection
- Current limitation
- Short circuit protection
- Thermal shutdown with restart
- ESD - Protection
- Overvoltage protection (including load dump)
- Fast demagnetization of inductive loads
- Reverse battery protection with external resistor
- Open drain diagnostic output
- CMOS compatible input
- Loss of GND and loss of V_{bb} protection
- Very low standby current

Product Summary

Overvoltage protection	$V_{bb(AZ)}$	41	V
Operating voltage	$V_{bb(on)}$	5 ... 34	V
On-state resistance	R_{ON}	350	m Ω
Nominal load current	$I_{L(nom)}$	0.4	A
Operating temperature	T_a	-30...+85	$^{\circ}\text{C}$



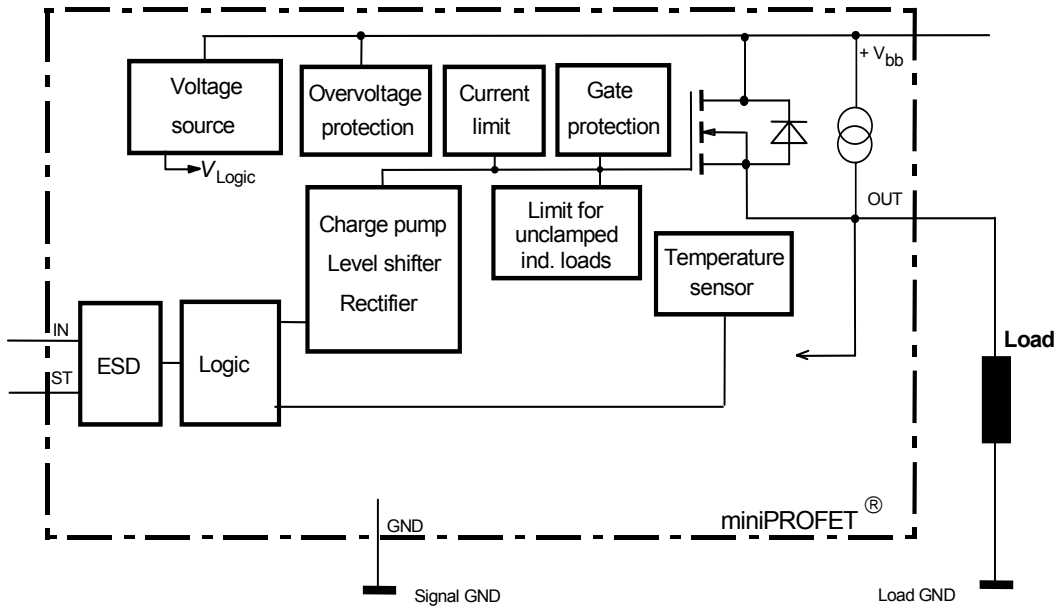
Application

- All types of resistive, inductive and capacitive loads
- μC compatible power switch for 12 V and 24 V DC industrial applications
- Replaces electromechanical relays and discrete circuits

General Description

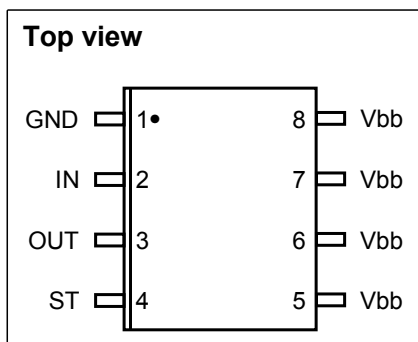
N channel vertical power FET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS[®] technology. Providing embedded protective functions.

Block Diagram



Pin	Symbol	Function
1	GND	Logic ground
2	IN	Input, activates the power switch in case of logic high signal
3	OUT	Output to the load
4	ST	Diagnostic feedback
5	Vbb	Positive power supply voltage
6	Vbb	Positive power supply voltage
7	Vbb	Positive power supply voltage
8	Vbb	Positive power supply voltage

Pin configuration



Maximum Ratings at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Supply voltage	V_{bb}	40	V
Supply voltage for full short circuit protection	$V_{bb(SC)}$	V_{bb}	
Continuous input voltage	V_{IN}	-10 ... +16	
Load current (Short - circuit current, see page 5)	I_L	self limited	A
Current through input pin (DC)	I_{IN}	± 5	mA
Junction temperature	T_j	150	°C
Operating temperature	T_a	-30...+85	
Storage temperature	T_{stg}	-40 ... +105	
Power dissipation ¹⁾	P_{tot}	1.5	W
Inductive load switch-off energy dissipation ¹⁾²⁾ single pulse, (see page 9) $T_j = 150\text{ °C}$, $V_{bb} = 13.5\text{ V}$, $I_L = 0.3\text{ A}$	E_{AS}	800	mJ
Load dump protection ²⁾ $V_{LoadDump}^{3)} = V_A + V_S$ $R_f = 2\Omega$, $t_d = 400\text{ms}$, $V_{IN} = \text{low or high}$, $V_A = 13.5\text{V}$ $R_L = 45\ \Omega$	$V_{Loaddump}$	60	V
Electrostatic discharge voltage (Human Body Model) according to ANSI EOS/ESD - S5.1 - 1993 ESD STM5.1 - 1998 Input pin all other pins	V_{ESD}	± 1 ± 5	kV

Thermal Characteristics

Thermal resistance @ min. footprint	$R_{th(JA)}$	-	95	-	K/W
Thermal resistance @ 6 cm ² cooling area ¹⁾	$R_{th(JA)}$	-	70	83	

¹⁾Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm² (one layer, 70µm thick) copper area for drain connection. PCB is vertical without blown air. (see page 17)

²⁾not subject to production test, specified by design

³⁾ $V_{Loaddump}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839 .

Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND pin, e.g. with a 150Ω resistor in GND connection. A resistor for the protection of the input is integrated.

Electrical Characteristics

Parameter and Conditions at $T_j = -40\dots+150^\circ\text{C}$, $V_{bb} = 13,5\text{V}$, unless otherwise specified	Symbol	Values			Unit
		min.	typ.	max.	

Load Switching Capabilities and Characteristics

On-state resistance $T_j = 25^\circ\text{C}$, $I_L = 0.3\text{ A}$, $V_{bb} = 9\dots40\text{ V}$ $T_j = 150^\circ\text{C}$	R_{ON}	- -	250 450	350 700	$\text{m}\Omega$
Nominal load current Device on PCB 1)2) $T_C = 85^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$	$I_{L(\text{nom})}$	0.4	-	-	A
Turn-on time to 90% V_{OUT} $R_L = 47\ \Omega$, $V_{IN} = 0$ to 10 V	t_{on}	-	-	140	μs
Turn-off time to 10% V_{OUT} $R_L = 47\ \Omega$, $V_{IN} = 10$ to 0 V	t_{off}	-	-	170	
Slew rate on 10 to 30% V_{OUT} , $R_L = 47\ \Omega$	dV/dt_{on}	-	-	2	$\text{V}/\mu\text{s}$
Slew rate off 70 to 40% V_{OUT} , $R_L = 47\ \Omega$	$-dV/dt_{off}$	-	-	2	

Operating Parameters

Operating voltage	$V_{bb(\text{on})}$	5	-	34	V
Undervoltage shutdown of charge pump	$V_{bb(\text{under})}$	-	-	5	
Undervoltage restart of charge pump	$V_{bb(\text{u cp})}$	-	-	5.5	
Standby current $V_{IN} = 0\text{ V}$	$I_{bb(\text{off})}$	-	-	26	μA
Leakage output current (included in $I_{bb(\text{off})}$)	$I_{L(\text{off})}$	-	-	12	
Operating current $V_{IN} = \text{high}$	I_{GND}	-	-	1.3	mA

¹Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air. (see page 17)

²Nominal load current is limited by current limitation (see page 5)

Electrical Characteristics

Parameter and Conditions at $T_j = -40\dots+150^\circ\text{C}$, $V_{bb} = 13,5\text{V}$, unless otherwise specified	Symbol	Values			Unit
		min.	typ.	max.	

Protection Functions¹⁾

Initial peak short circuit current limit (pin 5 to 3) $T_j = -40^\circ\text{C}$, $V_{bb} = 20\text{V}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	$I_{L(SCp)}$	- - 0.4	- 1.2 -	2 - -	A
Repetitive short circuit current limit $T_j = T_{jt}$ (see timing diagrams)	$I_{L(SCr)}$	-	1	-	
Output clamp (inductive load switch off) at $V_{OUT} = V_{bb} - V_{ON(CL)}$, $I_{bb} = 4\text{mA}$	$V_{ON(CL)}$	41	47	-	V
Overvoltage protection ²⁾ $I_{bb} = 4\text{mA}$	$V_{bb(AZ)}$	41	-	-	
Thermal overload trip temperature	T_{jt}	150	-	-	$^\circ\text{C}$
Thermal hysteresis	ΔT_{jt}	-	10	-	K

Reverse Battery

Reverse battery ³⁾	$-V_{bb}$	-	-	32	V
Drain-source diode voltage ($V_{OUT} > V_{bb}$) $T_j = 150^\circ\text{C}$	$-V_{ON}$	-	600	-	mV

¹⁾Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

²⁾ see also $V_{ON(CL)}$ in circuit diagram on page 8

³⁾Requires a $150\ \Omega$ resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Power dissipation is higher compared to normal operating conditions due to the voltage drop across the drain-source diode. The temperature protection is not active during reverse current operation! Input current has to be limited (see max. ratings page 3).

Electrical Characteristics

Parameter at $T_j = -40...+150^\circ\text{C}$, $V_{bb} = 13,5\text{V}$, unless otherwise specified	Symbol	Values			Unit
		min.	typ.	max.	
Input and Status feedback					
Input turn-on threshold voltage	$V_{IN(T+)}$	-	-	2.2	V
Input turn-off threshold voltage	$V_{IN(T-)}$	0.8	-	-	
Input threshold hysteresis	$\Delta V_{IN(T)}$	-	0.3	-	
Off state input current $V_{IN} = 0.7\text{ V}$	$I_{IN(off)}$	1	-	30	μA
On state input current $V_{IN} = 5\text{ V}$	$I_{IN(on)}$	1	-	30	
Status output (open drain), Zener limit voltage $I_{ST} = 1.6\text{ mA}$	$V_{ST(high)}$	5.4	6.1	-	V
Status output (open drain), ST low voltage $T_j = -40...+25^\circ\text{C}$, $I_{ST} = 1.6\text{ mA}$ $T_j = 150^\circ\text{C}$, $I_{ST} = 1.6\text{ mA}$	$V_{ST(low)}$	-	-	0.4	
		-	-	0.6	
Status invalid after input slope ¹⁾	$t_{d(ST)}$	-	300	600	μs
Input resistance (see page 8)	R_I	1.5	3.5	5	$\text{k}\Omega$

Diagnostic Characteristics

Short circuit detection voltage	$V_{OUT(SC)}$	-	2.8	-	V
Open load detection voltage	$V_{OUT(OL)}$	-	3	-	
Openload detection current included in standby current $I_{bb(off)}$	$I_{L(OL)}$	-	5	-	μA

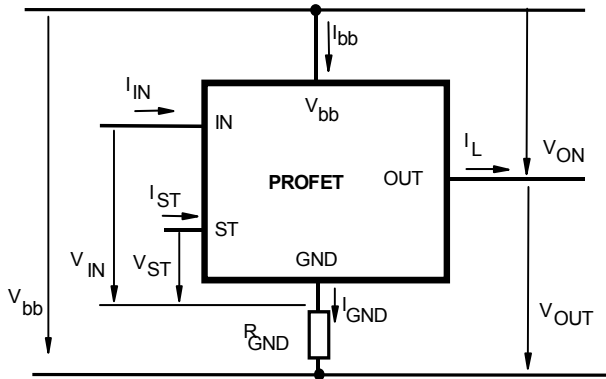
¹⁾no delay time after overtemperature switch off and short circuit in on-state

	Input level	Output level	Status
Normal operation	L	L	L
	H	H	L
Short circuit to GND	L	L	L
	H	L *	H
Short circuit to V_{bb} (in off-state)	L	H	H
	H	H	L
Overload	L	L	L
	H	H **	L
Overtemperature	L	L	L
	H	L	H
Open Load in off-state	L	H	H
	H	H	L

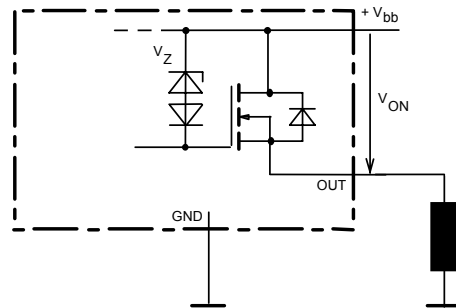
*) Out ="L": $V_{OUT} < 2V$ typ.

***) Out ="H": $V_{OUT} > 2V$ typ.

Terms

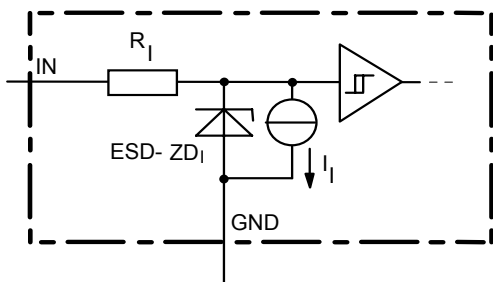


Inductive and overvoltage output clamp



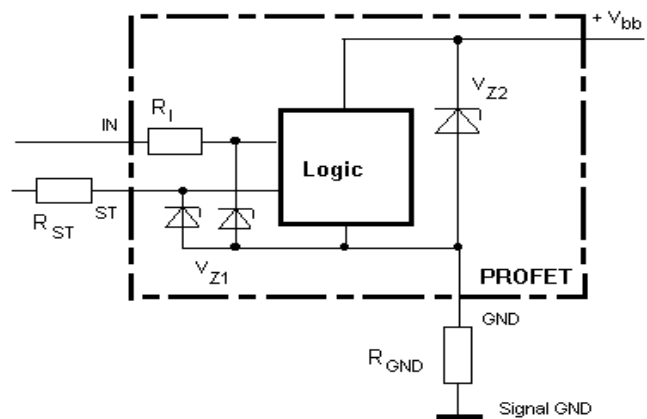
V_{ON} clamped to 47V typ.

Input circuit (ESD protection)



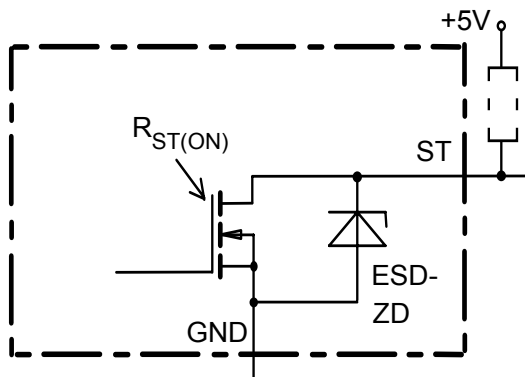
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended

Overvoltage protection of logic part

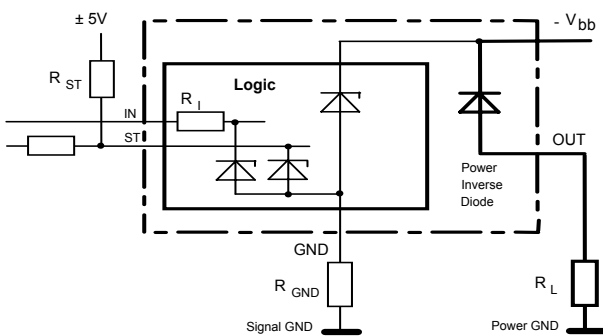


$V_{Z1}=6.1V$ typ., $V_{Z2}=V_{bb(AZ)}=47V$ typ.,
 $R_I=3.5\text{ k}\Omega$ typ., $R_{GND}=150\Omega$

Status output



Reverse battery protection

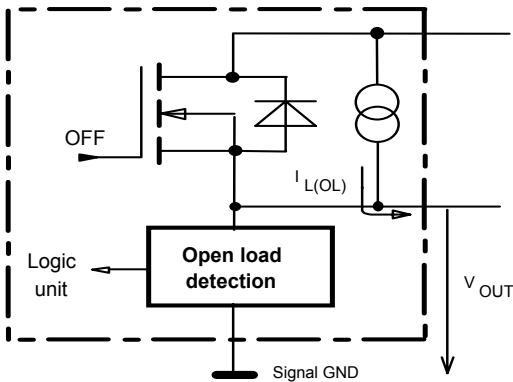


$R_{GND}=150\Omega$, $R_I=3.5\text{ k}\Omega$ typ.,
 Temperature protection is not active during inverse current

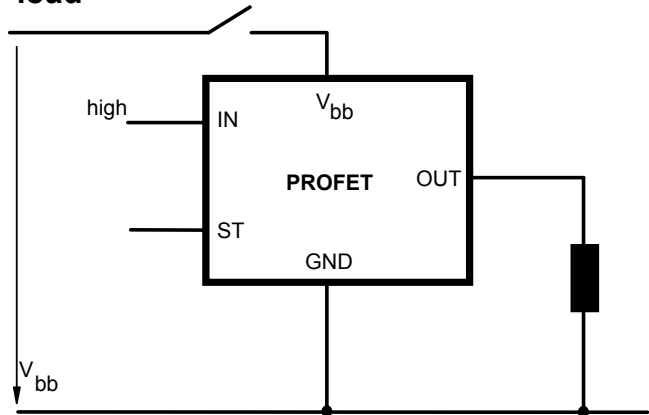
Open-load detection

OFF-state diagnostic condition:

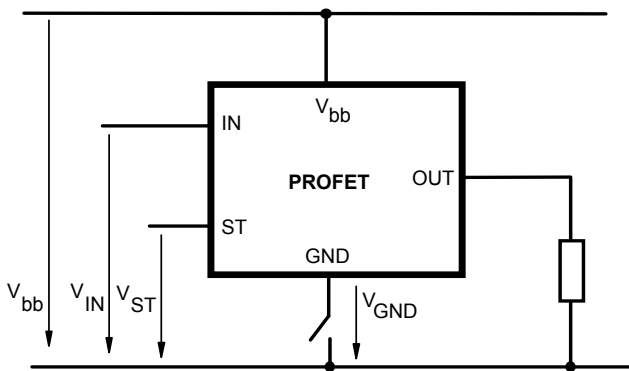
$V_{OUT} > 3V$ typ.; $I_N=low$



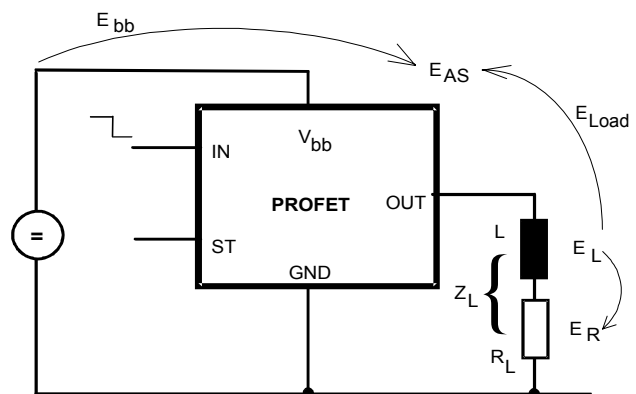
V_{bb} disconnect with charged inductive load



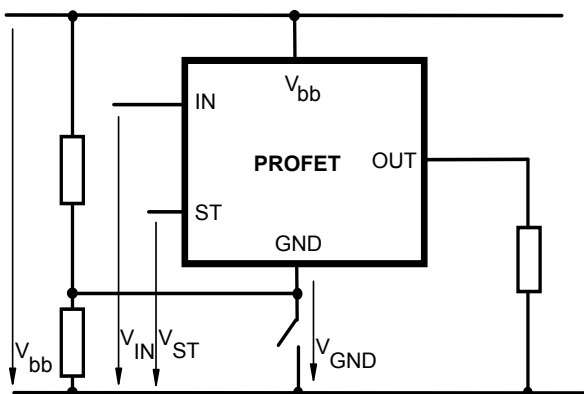
GND disconnect



Inductive Load switch-off energy dissipation



GND disconnect with GND pull up



Energy stored in load inductance: $E_L = \frac{1}{2} * L * I_L^2$

While demagnetizing load inductance,

the energy dissipated in PROFET is

$$E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} * i_L(t) dt,$$

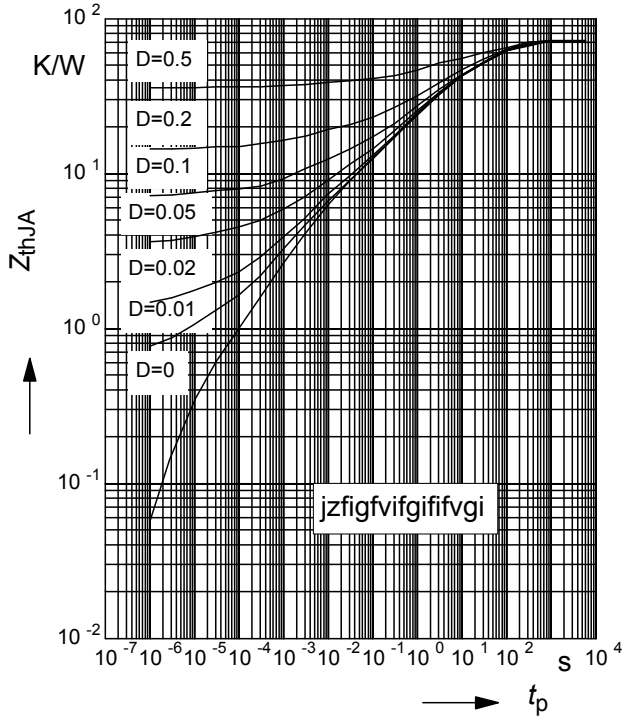
with an approximate solution for $R_L > 0\Omega$:

$$E_{AS} = \frac{I_L * L}{2 * R_L} * (V_{bb} + |V_{OUT(CL)}|) * \ln\left(1 + \frac{I_L * R_L}{|V_{OUT(CL)}|}\right)$$

Typ. transient thermal impedance

$Z_{thJA} = f(t_p)$ @ 6cm² heatsink area

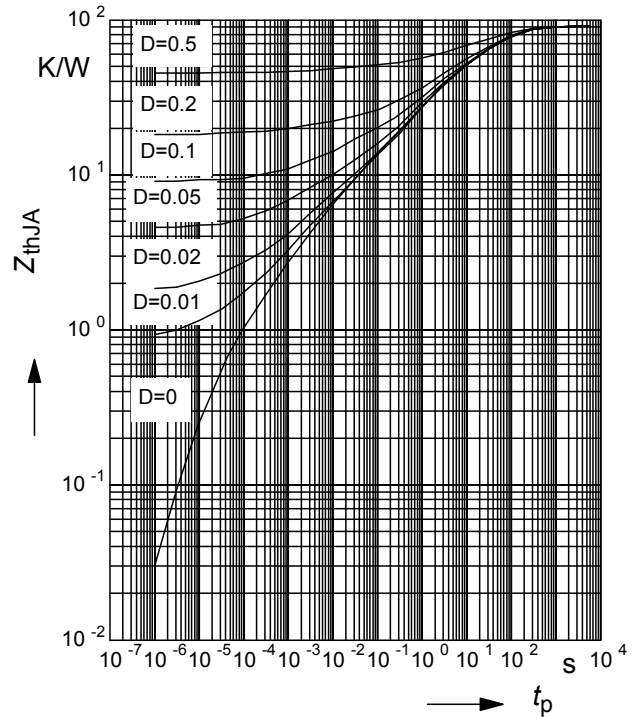
Parameter: $D = t_p / T$



Typ. transient thermal impedance

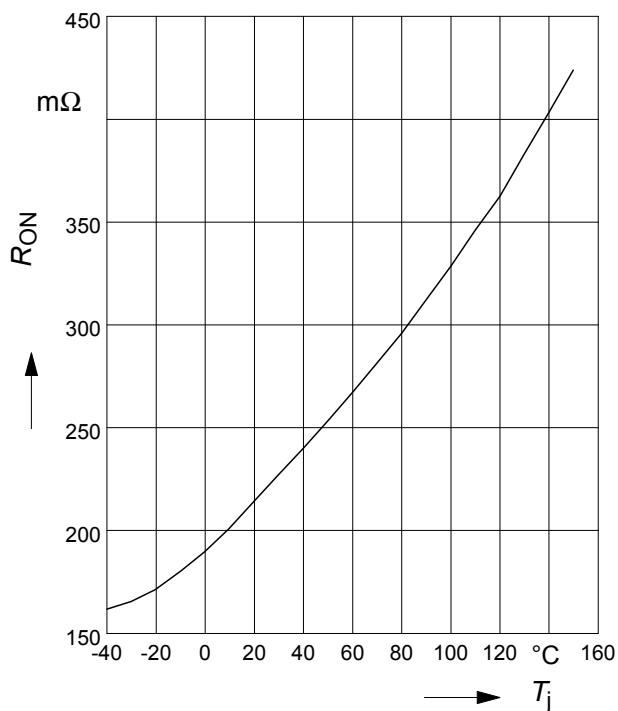
$Z_{thJA} = f(t_p)$ @ minimal footprint

Parameter: $D = t_p / T$



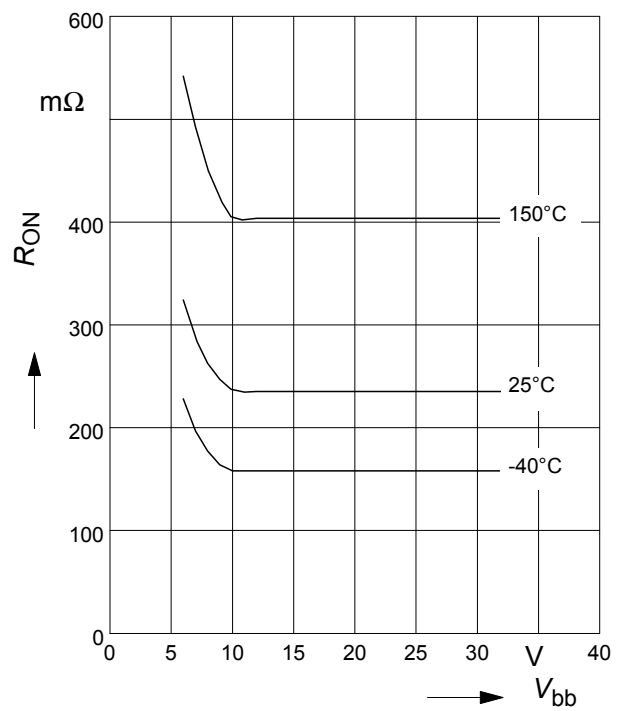
Typ. on-state resistance

$R_{ON} = f(T_j)$; $V_{bb} = 13,5V$; $V_{in} = high$



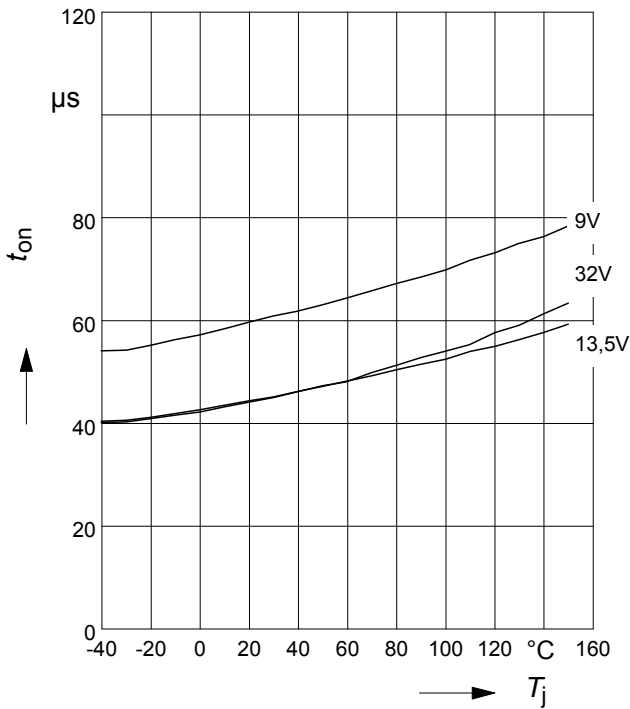
Typ. on-state resistance

$R_{ON} = f(V_{bb})$; $I_L = 0.3A$; $V_{in} = high$



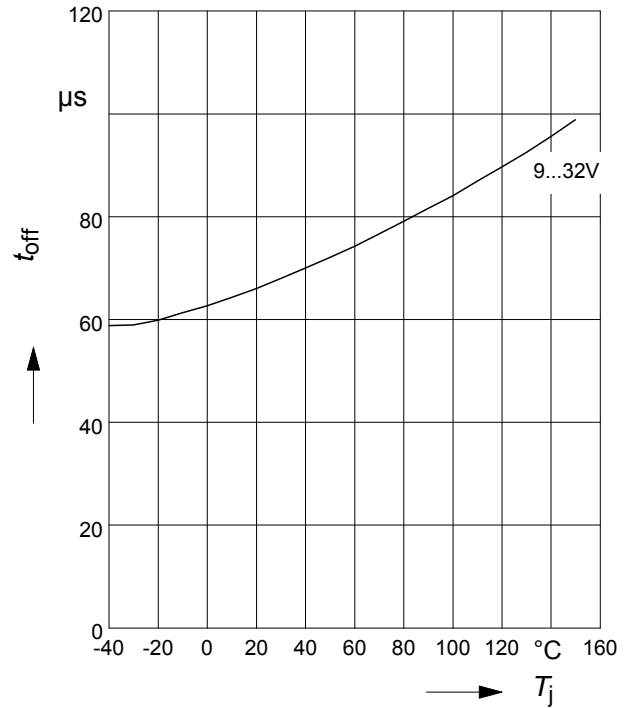
Typ. turn on time

$t_{on} = f(T_j); R_L = 47\Omega$



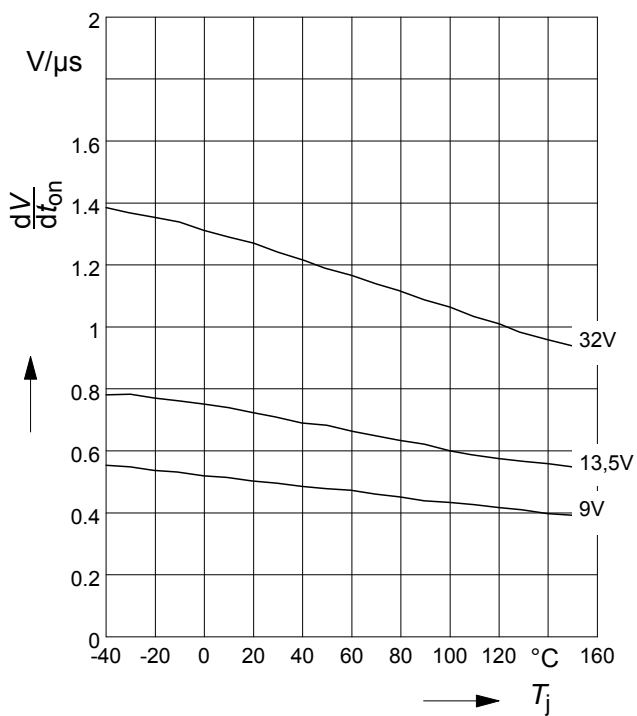
Typ. turn off time

$t_{off} = f(T_j); R_L = 47\Omega$



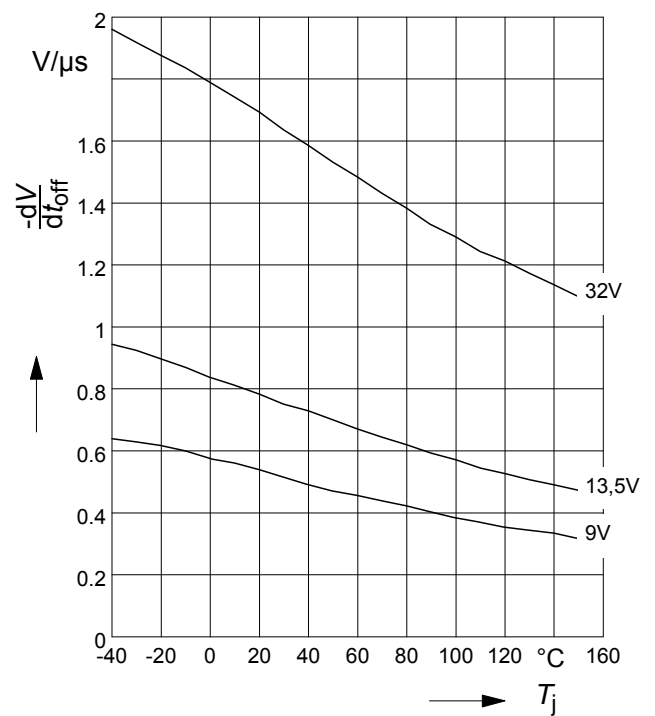
Typ. slew rate on

$dV/dt_{on} = f(T_j); R_L = 47\Omega$



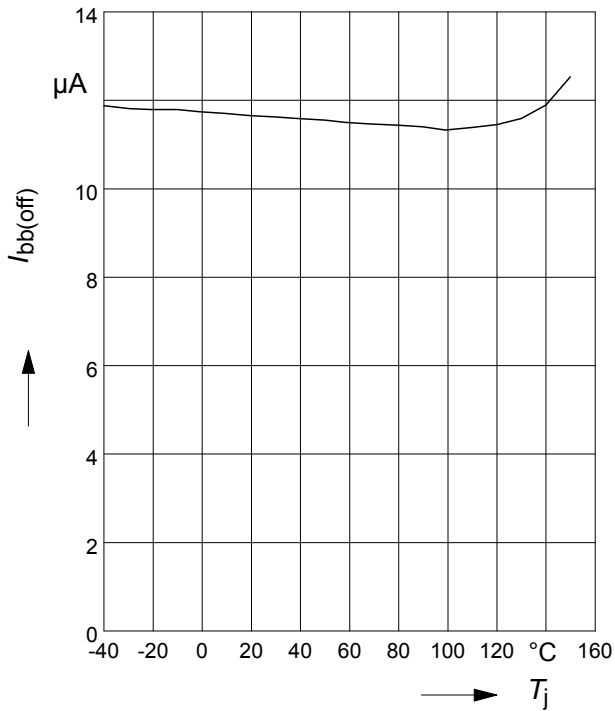
Typ. slew rate off

$-dV/dt_{off} = f(T_j); R_L = 47\Omega$



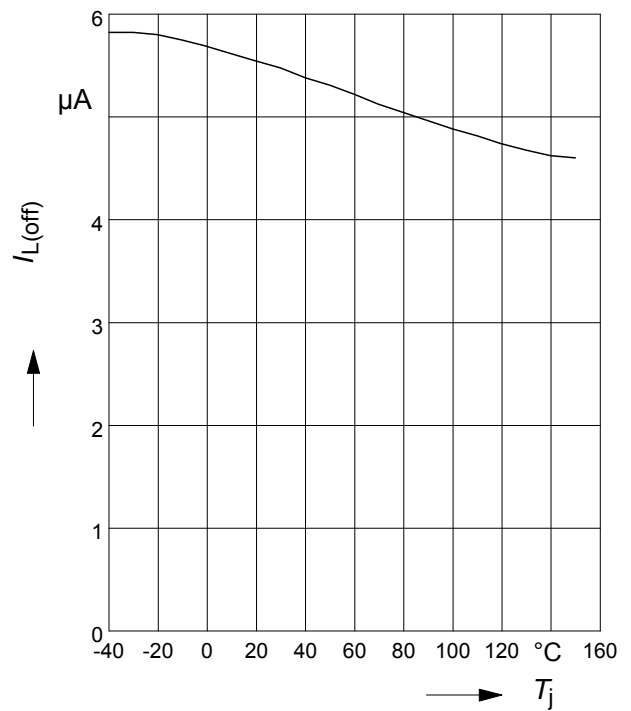
Typ. standby current

$I_{bb(off)} = f(T_j) ; V_{bb} = 32V ; V_{IN} = low$



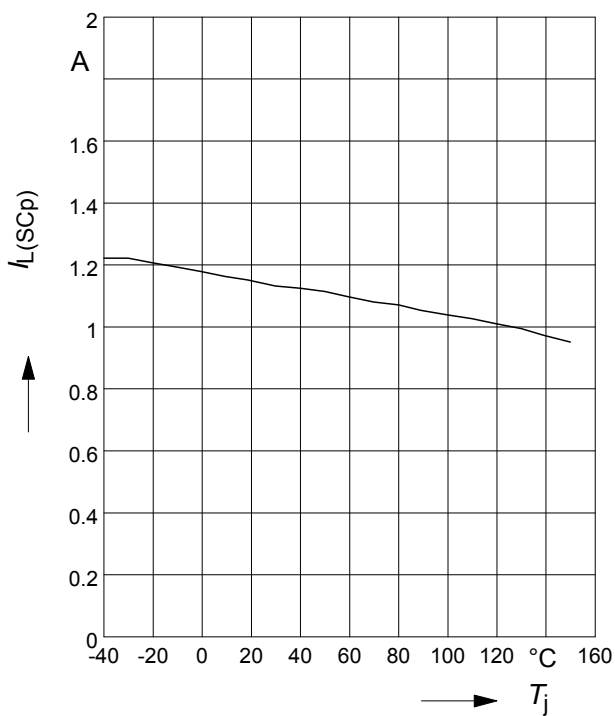
Typ. leakage current

$I_{L(off)} = f(T_j) ; V_{bb} = 32V ; V_{IN} = low$



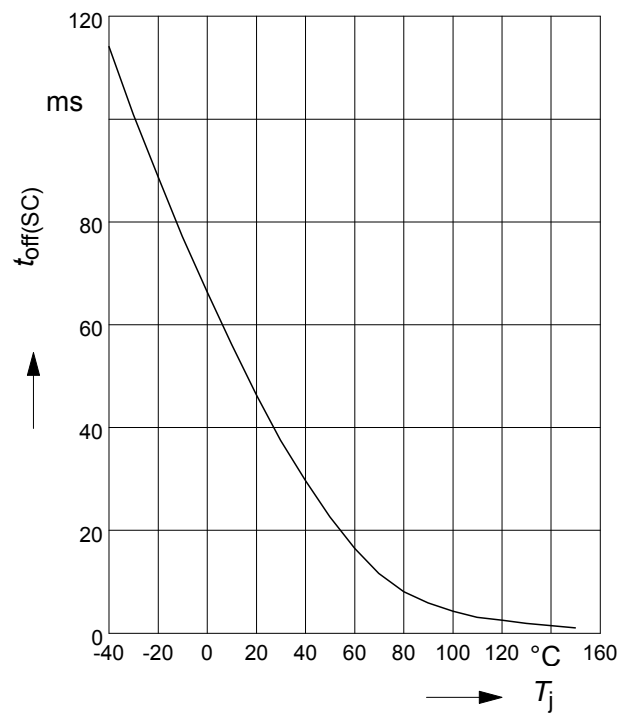
Typ. initial peak short circuit current limit

$I_{L(SCp)} = f(T_j) ; V_{bb} = 20V$



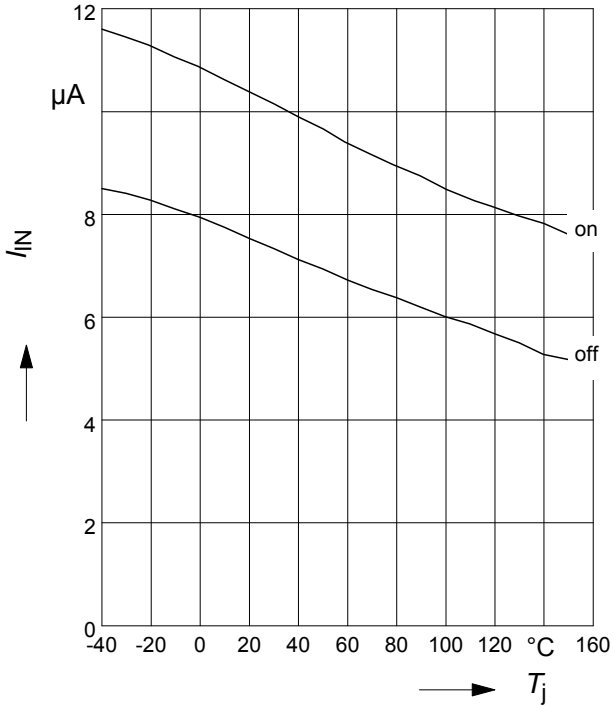
Typ. initial short circuit shutdown time

$t_{off(SC)} = f(T_{j,start}) ; V_{bb} = 20V$



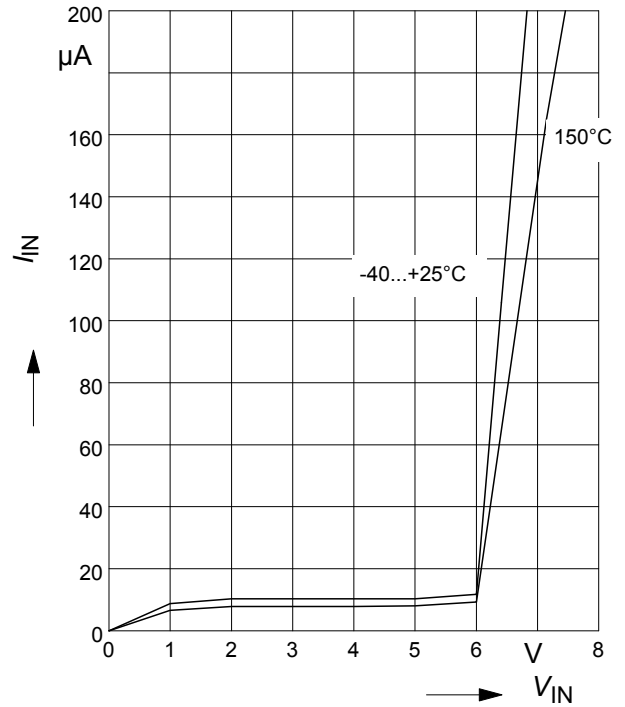
Typ. input current

$I_{IN(on/off)} = f(T_j)$; $V_{bb} = 13,5V$; $V_{IN} = \text{low/high}$
 $V_{INlow} \leq 0,7V$; $V_{INhigh} = 5V$



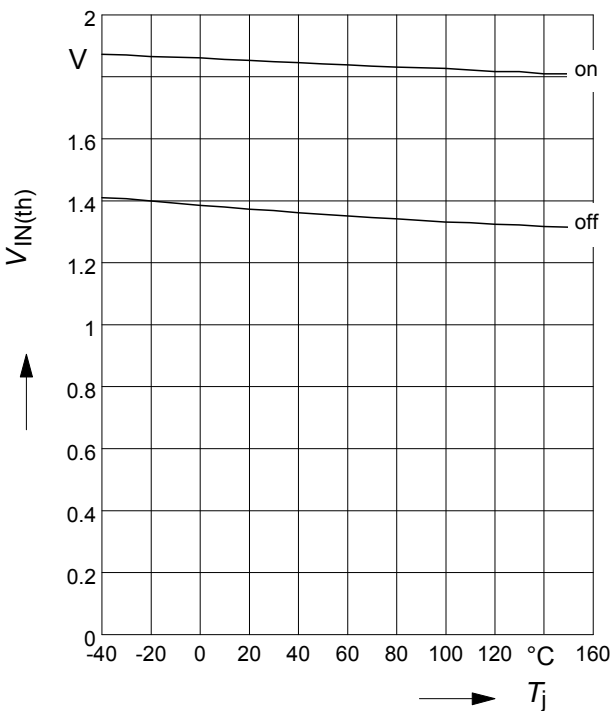
Typ. input current

$I_{IN} = f(V_{IN})$; $V_{bb} = 13.5V$



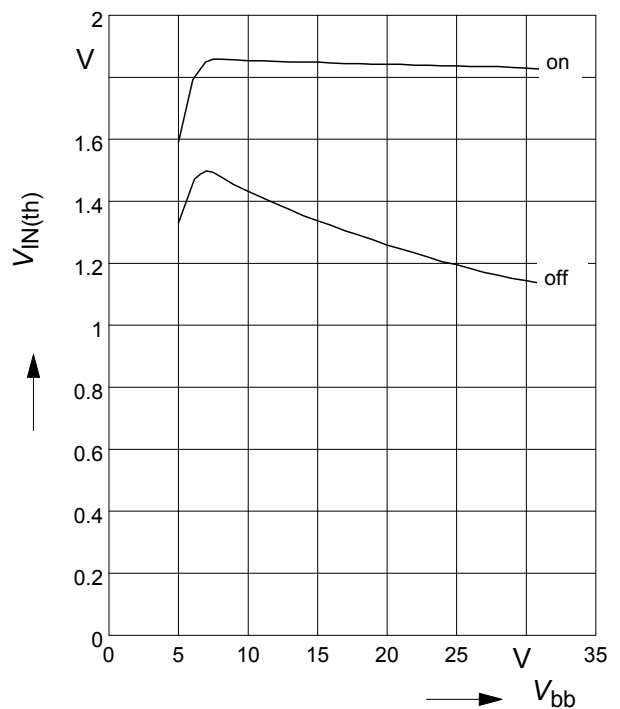
Typ. input threshold voltage

$V_{IN(th)} = f(T_j)$; $V_{bb} = 13,5V$



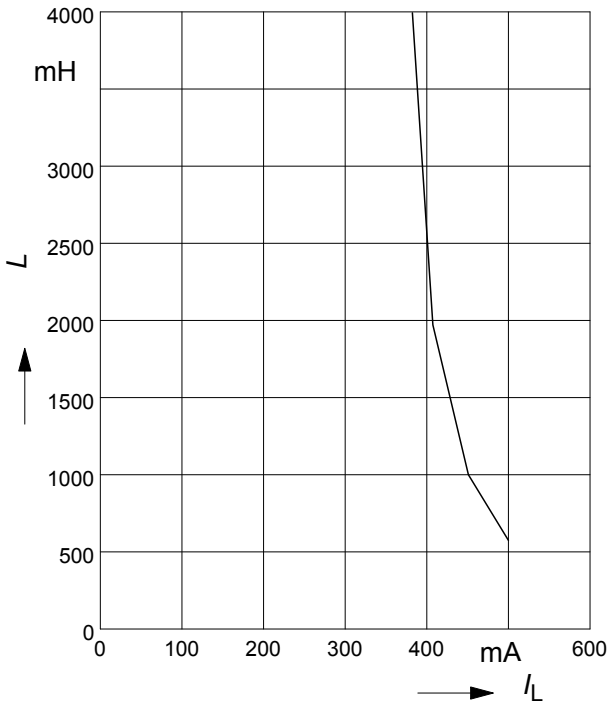
Typ. input threshold voltage

$V_{IN(th)} = f(V_{bb})$; $T_j = 25^{\circ}C$



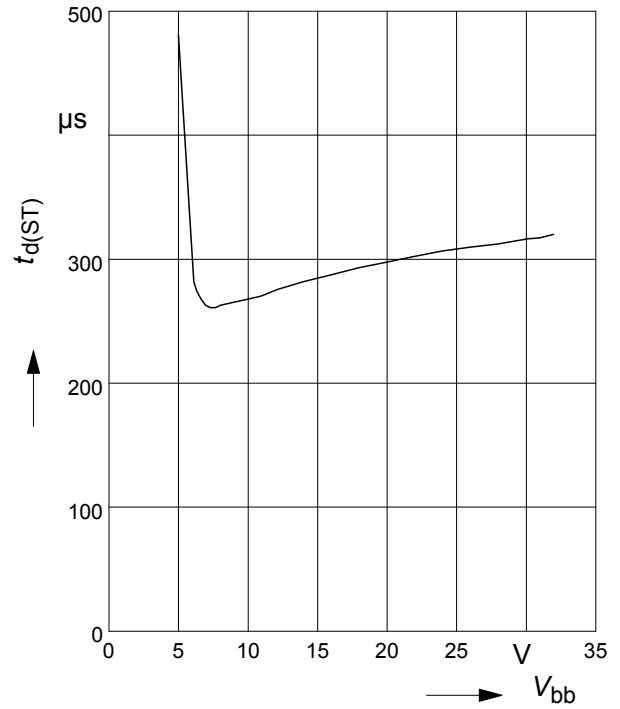
Maximum allowable load inductance for a single switch off

$L = f(I_L)$; $T_{jstart}=150^{\circ}C$, $V_{bb}=13.5V$, $R_L=0\Omega$



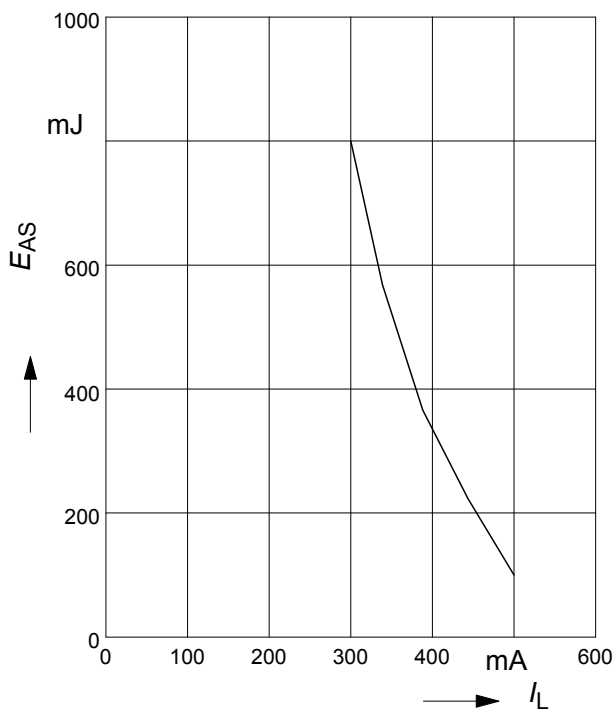
Typ. status delay time

$t_{d(ST)} = f(V_{bb})$; $T_j = 25^{\circ}C$



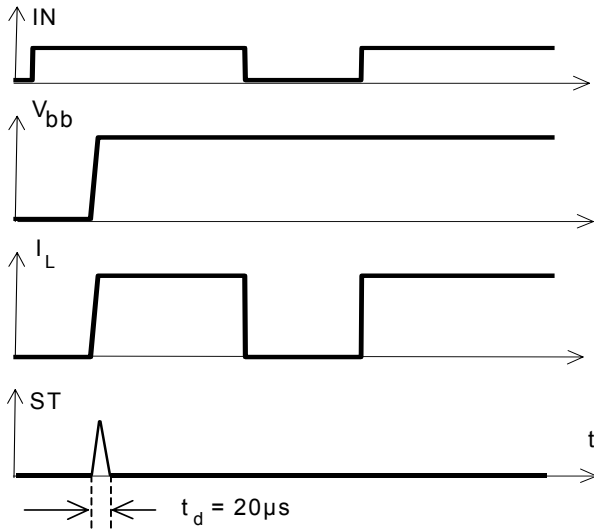
Maximum allowable inductive switch-off energy, single pulse

$E_{AS} = f(I_L)$; $T_{jstart} = 150^{\circ}C$, $V_{bb} = 13.5V$



Timing diagrams

Figure 1a: V_{bb} turn on:



Invalid status during t_d

Figure 2b: Switching a lamp,

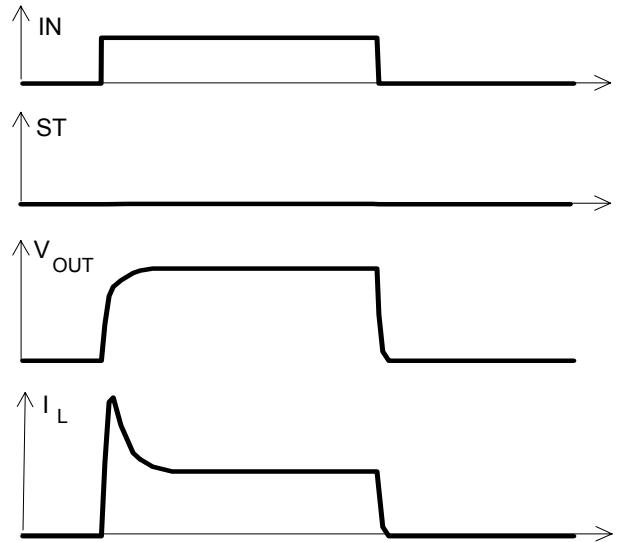


Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition

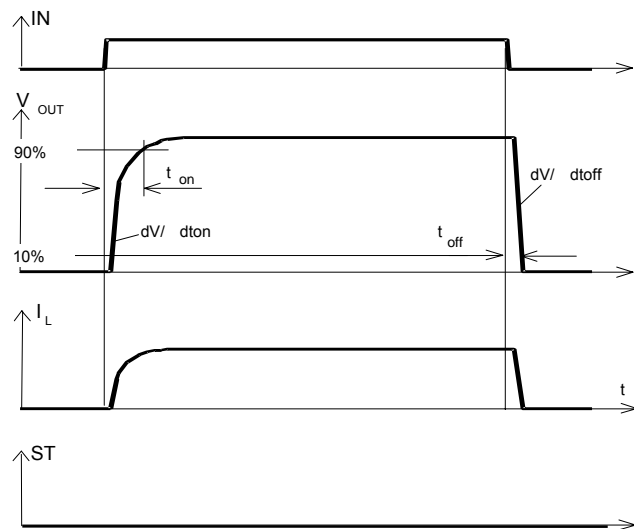


Figure 2c: Switching an inductive load

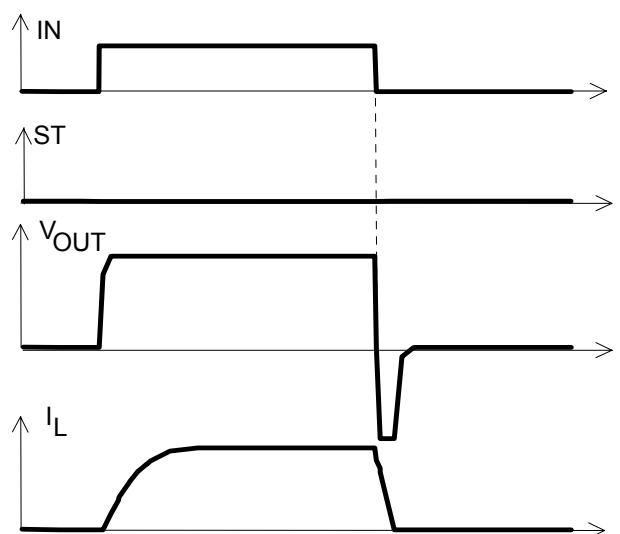
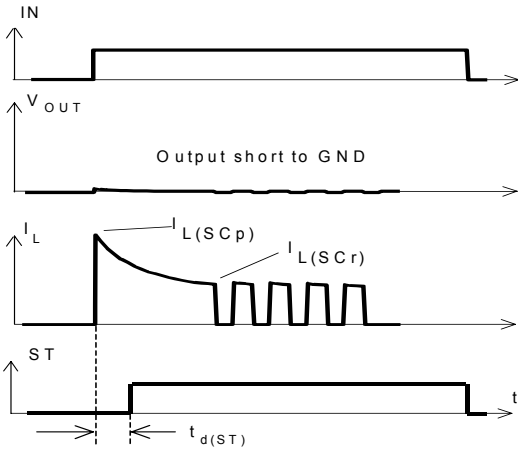


Figure 3a: Turn on into short circuit, shut down by overtemperature, restart by cooling



Heating up of the chip may require several milliseconds, depending on external conditions.

Figure 3b: Short circuit in on-state shut down by overtemperature, restart by cooling

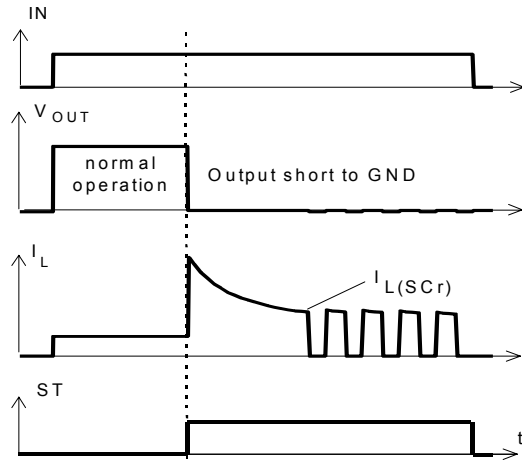


Figure 4: Overtemperature: Reset if $T_j < T_{jt}$

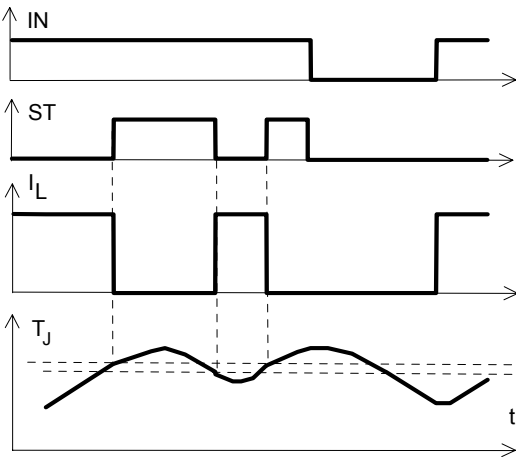
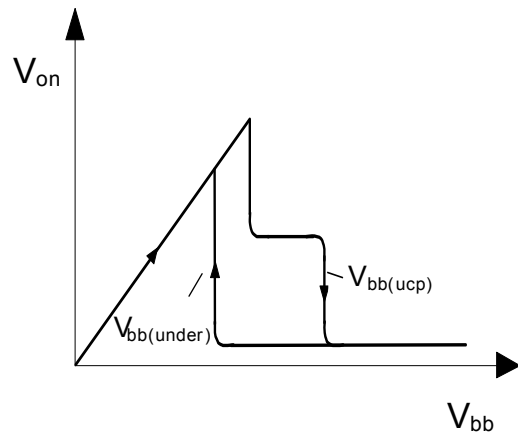


Figure 5: Undervoltage restart of charge pump



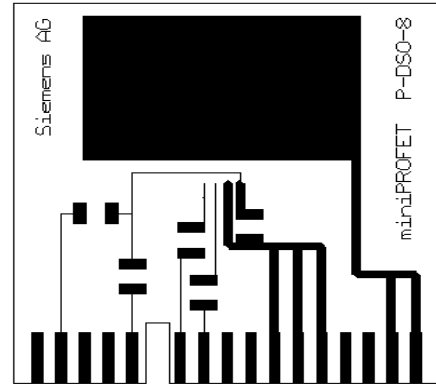
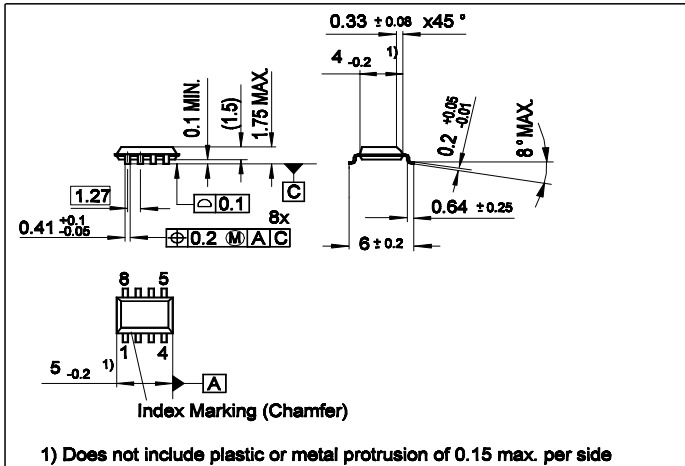
Package and ordering code

all dimensions in mm

Package:

Ordering code:

PG-DSO-8	SP000221229
----------	-------------



Printed circuit board (FR4, 1.5mm thick, one layer 70µm, 6cm² active heatsink area) as a reference for max. power dissipation P_{tot} nominal load current $I_{L(nom)}$ and thermal resistance R_{thja}

Published by
Infineon Technologies AG,
 St.-Martin-Strasse 53,
 D-81669 München
 © Infineon Technologies AG 2001
 All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as a guarantee of characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.